

REMARKS

Claims 13-35 are pending, with claims 13, 20 and 22 being independent. Claims 1-12 have been cancelled, claims 13, 20 and 22 have been amended to remove a limitation added in the prior response, and claims 34 and 35 have been added.

Figs. 1a and 1b have been amended to identify them as showing prior art.

Claims 13-33 have been rejected as being anticipated by Kuramasu. Applicants request reconsideration and withdrawal of this rejection because Kuramasu does not describe or suggest a semiconductor island having a channel length direction that is parallel or approximately parallel to a longitudinal edge of a heat absorbing layer, as recited in each of the independent claims. Rather, Kuramasu, in Fig. 13, describes a semiconductor island having a channel length direction that is perpendicular to a longitudinal edge of a heat absorbing layer.

In Kuramasu, the polycrystalline silicon thin film 2, which the Examiner has equated to the semiconductor island, has a channel length direction extending from the source electrode 6 to the drain electrode 7. See the current application at page 11, lines 17-20 (noting that the channel length direction corresponds to the direction of the current path). By contrast, as would have been readily recognized by one of skill in the art, the gate electrode 4, which the Examiner has equated to the heat absorbing layer, has a longitudinal edge that extends into the paper and perpendicular to the channel length direction. For at least this reason, applicant requests reconsideration and withdrawal of the rejection.